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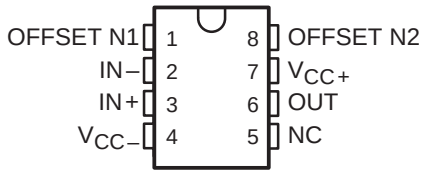
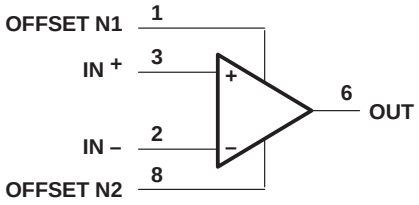
- **Low Noise**
- **No External Components Required**
- **Replaces Chopper Amplifiers at a Lower Cost**
- **Single-Chip Monolithic Fabrication**
- **Wide Input Voltage Range**
  0 to ±14 V Typ
- **Wide Supply Voltage Range**
  ±3 V to ±18 V
- **Essentially Equivalent to Fairchild μA714 Operational Amplifiers**
- **Direct Replacement for PMI OP07C and OP07D**

D OR P PACKAGE
(TOP VIEW)



NC – No internal connection

symbol



description

These devices represent a breakthrough in operational amplifier performance. Low offset and long-term stability are achieved by means of a low-noise, chopperless, bipolar-input-transistor amplifier circuit. For most applications, external components are not required for offset nulling and frequency compensation. The true differential input, with a wide input voltage range and outstanding common-mode rejection, provides maximum flexibility and performance in high-noise environments and in noninverting applications. Low bias currents and extremely high input impedances are maintained over the entire temperature range. The OP07 is unsurpassed for low-noise, high-accuracy amplification of very low-level signals.

These devices are characterized for operation from 0°C to 70°C.

AVAILABLE OPTIONS

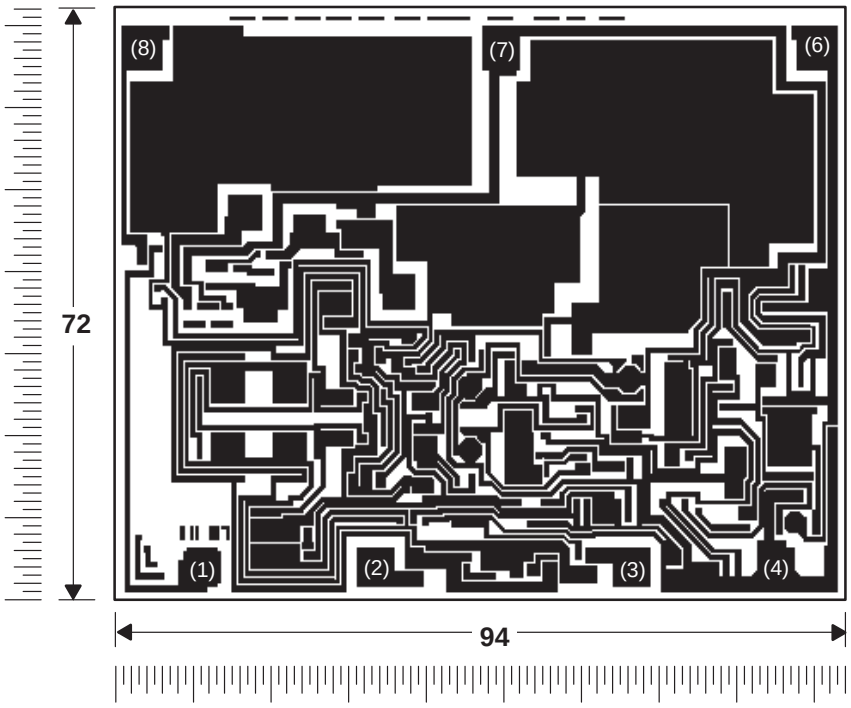
T_A	V_{IO}max AT 25°C	PACKAGED DEVICES		CHIP FORM (Y)
		SMALL OUTLINE (D)	PLASTIC DIP (P)	
0°C to 70°C	150 μV	OP07CD OP07DD	OP07CP OP07DP	OP07Y

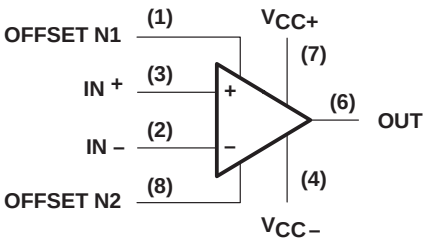
The D package is available taped and reeled. Add the suffix R to the device type (e.g., OP07CDR). The chip form is tested at T_A = 25°C.

OP07Y chip information

These chips, properly assembled, display characteristics similar to the OP07. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.

BONDING PAD ASSIGNMENTS





CHIP THICKNESS: 15 TYPICAL

BONDING PADS: 4 × 4 MINIMUM

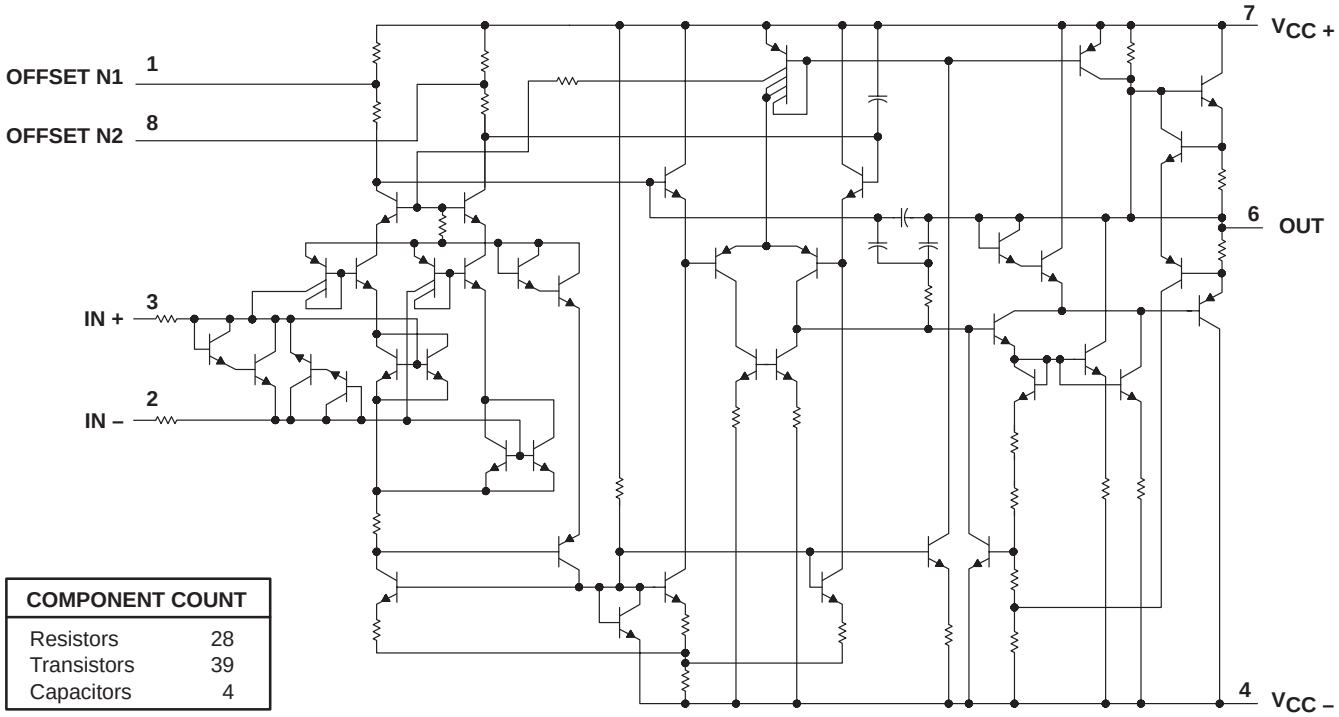
$T_J$max = 150°C

TOLERANCES ARE ± 10%.

ALL DIMENSIONS ARE IN MILS.

PIN (4) IS INTERNALLY CONNECTED TO BACKSIDE OF CHIP.

schematic



COMPONENT COUNT	
Resistors	28
Transistors	39
Capacitors	4

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V_{CC+} (see Note 1) . . . . . 22 V
Supply voltage, V_{CC-} . . . . . –22 V
Differential input voltage (see Note 2) . . . . . ±30 V
Input voltage, V_I (either input, see Note 3) . . . . . ±22 V
Duration of output short circuit (see Note 4) . . . . . unlimited
Continuous total dissipation at (or below) 25°C free-air temperature (see Note 5) . . . . . 500 mW
Operating free-air temperature range, T_A . . . . . 0°C to 70°C
Storage temperature range . . . . . –65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds . . . . . 260°C

NOTES: 1. All voltage values, unless otherwise noted, are with respect to the midpoint between V_{CC+} and V_{CC-}.
2. Differential voltages are at IN+ with respect to IN–.
3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.
4. The output may be shorted to ground or either power supply.
5. For operation above 64°C free-air temperature, derate the D package to 464 mW at 70°C at the rate of 5.8 mW/°C.

recommended operating conditions

		MIN	MAX	UNIT
Supply voltage, $V_{CC\pm}$		±3	±18	V
Common-mode input voltage, V_{IC}	$V_{CC\pm}$ = ±15 V	–13	13	V
Operating free-air temperature, T_A		0	70	°C

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electrical characteristics at specified free-air temperature, $V_{CC}\pm$ = ±15 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS†		T_A	OP07C			OP07D			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO}	Input offset voltage	V_O = 0,	R_S = 50 Ω	25°C		60	150		60	150	µV
				0°C to 70°C		85	250		85	250	
α_{VIO}	Temperature coefficient of input offset voltage	V_O = 0,	R_S = 50 Ω	0°C to 70°C		0.5	1.8		0.7	2.5	µV/°C
	Long-term drift of input offset voltage	See Note 6				0.4			0.5		µV/mo
	Offset adjustment range	R_S = 20 kΩ,	See Figure 1	25°C		±4			±4		mV
I_{IO}	Input offset current			25°C		0.8	6		0.8	6	nA
				0°C to 70°C		1.6	8		1.6	8	
α_{IIO}	Temperature coefficient of input offset current			0°C to 70°C		12	50		12	50	pA/°C
I_{IB}	Input bias current			25°C		±1.8	±7		±2	±12	nA
				0°C to 70°C		±2.2	±9		±3	±14	
α_{IIB}	Temperature coefficient of input bias current			0°C to 70°C		18	50		18	50	pA/°C
V_{ICR}	Common-mode input voltge range			25°C	±13	±14		±13	±14		V
				0°C to 70°C	±13	±13.5		±13	±13.5		
V_{OM}	Peak output voltage	R_L ≥ 10 kΩ		25°C	±12	±13		±12	±13		V
		R_L ≥ 2 kΩ			±11.5	±12.8		±11.5	±12.8		
		R_L ≥ 1 kΩ				±12			±12		
		R_L ≥ 2 kΩ		0°C to 70°C	±11	±12.6		±11	±12.6		
A_{VD}	Large-signal differential voltage amplification	$V_{CC\pm}$ = ±3 V, R_L ≥ 500 kΩ	V_O = ±0.5 V,	25°C	100	400			400		V/mV
		V_O = ±10 V,	R_L = 2 kΩ	25°C	120	400		120	400		
				0°C to 70°C	100	400		100	400		
B_1	Unity-gain bandwidth			25°C	0.4	0.6		0.4	0.6		MHz
r_i	Input resistance			25°C	8	33		7	31		MΩ
CMRR	Common-mode rejection ratio	V_{IC} = ±13 V,	R_S = 50 Ω	25°C	100	120		94	110		dB
				0°C to 70°C	97	120		94	106		
k_{SVS}	Supply voltage sensitivity ($\Delta V_{IO}/\Delta V_{CC}$)	$V_{CC\pm}$ = ±3 V to ±18 V, R_S = 50 Ω		25°C		7	32		7	32	µV/V
				0°C to 70°C		10	51		10	51	
P_D	Power dissipation	V_O = 0,	No load	25°C		80	150		80	150	mW
		$V_{CC\pm}$ = ±3 V, No load	V_O = 0,			4	8		4	8	

† All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise noted.

NOTE 6: Since long-term drift cannot be measured on the individual devices prior to shipment, this specification is not intended to be a warranty. It is an engineering estimate of the averaged trend line of drift versus time over extended periods after the first thirty days of operation.

operating characteristics, $V_{CC\pm}$ = ±15 V, T_A = 25°C

PARAMETER		TEST CONDITIONS†	OP07C			OP07D			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_n	Equivalent input noise voltage	f = 10 Hz		10.5			10.5		nV/√Hz
		f = 100 Hz		10.2			10.3		
		f = 1 kHz		9.8			9.8		
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 10 Hz		0.38			0.38		µV
I_n	Equivalent input noise current	f = 10 Hz		0.35			0.35		pA/√Hz
		f = 100 Hz		0.15			0.15		
		f = 1 kHz		0.13			0.13		
$I_{N(PP)}$	Peak-to-peak equivalent input noise current	f = 0.1 Hz to 10 Hz		15			15		pA
SR	Slew rate	$R_L \geq 2$ kΩ		0.3			0.3		V/µs

† All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise noted.

electrical characteristics, $V_{CC\pm}$ = ±15 V, T_A = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS†	OP07Y			UNIT
			MIN	TYP	MAX	
V_{IO}	Input offset voltage	R_S = 50 Ω		60	150	µV
	Long-term drift of input offset voltage	See Note 6		0.5		µV/mo
	Offset adjustment range	R_S = 20 kΩ, See Figure 1		±4		mV
I_{IO}	Input offset current			0.8	6	nA
I_{IB}	Input bias current			±2	±12	nA
V_{ICR}	Common-mode input voltage range		±13	±14		V
V_{OM}	Peak output voltage	$R_L \leq 10$ kΩ	±12	±13		V
		$R_L \leq 2$ kΩ	±11.5	±12.8		
		$R_L \leq 1$ kΩ		±12		
A_{VD}	Large-signal differential voltage amplification	$V_{CC\pm}$ = ±3 V, V_O = ±0.5 V, $R_L \leq 500$ kΩ		400		
		V_O = ±10 V, R_L = 2 kΩ	120	400		
B_1	Unity-gain bandwidth		0.4	0.6		MHz
r_i	Input resistance		7	31		MΩ
CMRR	Common-mode input resistance	V_{IC} = ±13 V, R_S = 50 Ω	94	110		dB
k_{SVS}	Supply-voltage rejection ratio ($\Delta V_{CC}/\Delta V_{IO}$)	$V_{CC\pm}$ = ±3 V to ±18 V, R_S = 50 Ω		7	32	µV/V
P_D	Power dissipation	V_O = 0, No load		80	150	MΩ
		$V_{CC\pm}$ = ±3 V, V_O = 0, No load		4	8	

NOTE 6: Since long-term drift cannot be measured on the individual devices prior to shipment, this specification is not intended to be a warranty. It is an engineering estimate of the averaged trend line of drift versus time over extended periods after the first thirty days of operation.

operating characteristics, $V_{CC\pm}$ = ±15 V, T_A = 25°C

PARAMETER		TEST CONDITIONS†	OP07Y			UNIT
			MIN	TYP	MAX	
V_n	Equivalent input noise voltage	f = 10 Hz		10.5		nV/√Hz
		f = 1 kHz		10.3		
		f = 0.1 Hz to 10 Hz		9.8		
$V_{N(PP)}$	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 10 Hz		0.38		µV
I_n	Equivalent input noise current	f = 10 Hz		0.35		pA/√Hz
		f = 100 Hz		0.15		
		f = 1 kHz		0.13		
$I_{N(PP)}$	Peak-to-peak equivalent input noise current	f = 0.1 Hz to 10 Hz		15		pA
SR	Slew rate	R_L = 2 kΩ		0.3		V/µs

† All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise noted.

APPLICATION INFORMATION

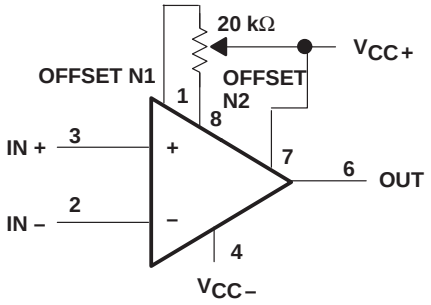

Figure 1. Input Offset Voltage Null Circuit

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